

TO-247-2L Plastic-Encapsulate Diodes

SUPER FAST RECOVER RECTIFIER

MAIN CHARACTERISTICS

I_O	30A
V_{RRM}	600V
T_{rr}	29ns
T_j	175°C
$V_{F(typ)}$	1.05V(@ $T_j=150^{\circ}C$)

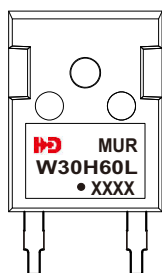
FEATURES

- Ultrafast Recovery Times and Low Recovery Loss
- Low Forward Voltage
- Low Reverse Leakage Current

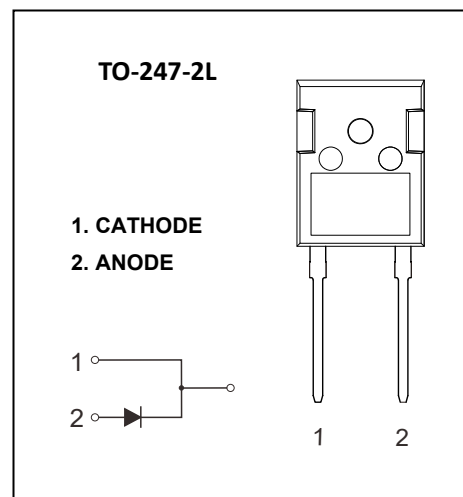
APPLICATIONS

Specifically designed to improve efficiency of PFC and output rectification stages of EV / HEV battery charging stations, booster stage of solar inverters and UPS applications, these devices are perfectly matched to operate with MOSFETs or high speed IGBTs.

MARKING



MURW30H60L = Device code
Solid dot = Green molding compound device
if none, the normal device
XXXX = Code



MAXIMUM RATINGS ($T_c=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	MURW30H60L	Unit
V_{RRM}	Peak Repetitive Reverse Voltage	600	V
V_R	DC Blocking Voltage		
$I_{F(AV)}$	Average Forward Current($T_c=130^{\circ}C$)	30	A
$I_{F(RMS)}$	RMS Forward Current($T_c=130^{\circ}C$)	42	A
I_{FSM}	Non-Repetitive Surge Forward Current (8.3ms)	344	A
P_D	Power dissipation	187.5	W
$R_{\theta JC}$	Thermal Resistance From Junction to Case	0.8	$^{\circ}C/W$
T_j	Operating Junction Temperature Range	-55 ~ +175	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55 ~ +175	$^{\circ}C$

Typical Characteristics

ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$ unless otherwise specified)

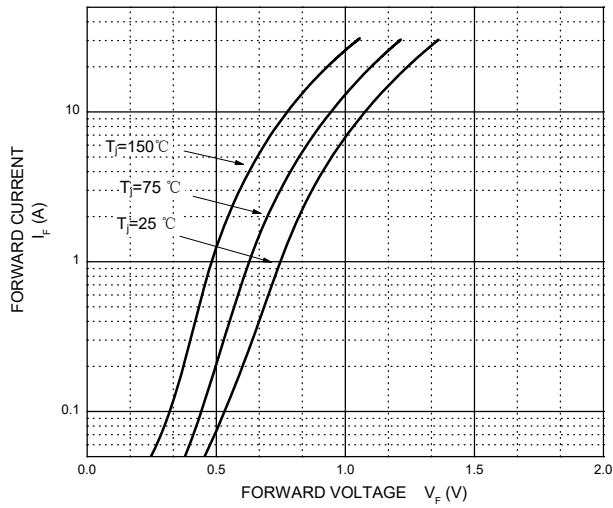
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)}$	Reverse Voltage	$I_R=100\mu\text{A}$	600			V
I_R	Reverse Current	$V_R=600\text{V}$			10	μA
					500	μA
V_F	Forward Voltage	$I_F=30\text{A}$		1.36	1.6	V
				1.05		V
C_{tot}	Total Capacitance	$V_R=200\text{V}, f=1\text{MHz}$		45		pF
t_{rr}	Reverse Recovery time	$I_F=0.5\text{A}, I_R=1\text{A}, I_{rr}=0.25\text{A}$		38		ns
		$I_F=1\text{A}, V_R=30\text{V}, di_F/dt=200\text{A}/\mu\text{s}$		29		ns

ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$ unless otherwise specified)

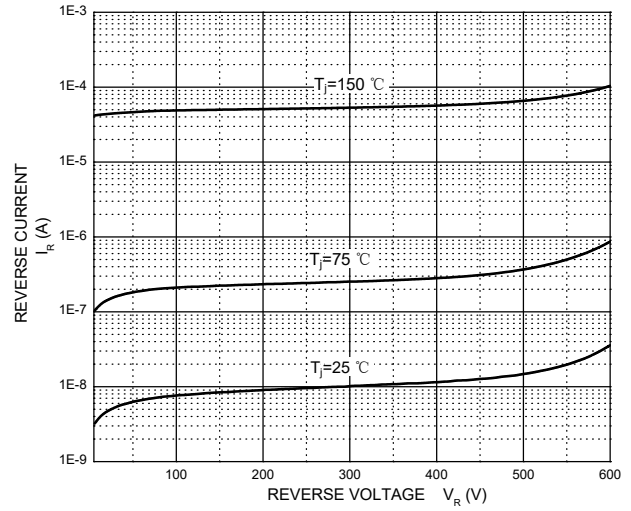
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t_{rr}	Reverse Recovery Time	$I_F=30\text{A}, V_R=400\text{V}, di_F/dt=200\text{A}/\mu\text{s}$		74		ns
I_{RRM}	Max. Reverse Recovery Current			4.5		A
Q_{rr}	Reverse Recovery Charge			202		nC
t_{rr}	Reverse Recovery Time	$I_F=30\text{A}, V_R=400\text{V}, di_F/dt=200\text{A}/\mu\text{s}, T_j=125^\circ\text{C}$		114		ns
I_{RRM}	Max. Reverse Recovery Current			11		A
Q_{rr}	Reverse Recovery Charge			680		nC
t_{rr}	Reverse Recovery Time	$I_F=30\text{A}, V_R=400\text{V}, di_F/dt=500\text{A}/\mu\text{s}, T_j=125^\circ\text{C}$		79		ns
I_{RRM}	Max. Reverse Recovery Current			24		A
Q_{rr}	Reverse Recovery Charge			1037		nC

Typical Characteristics

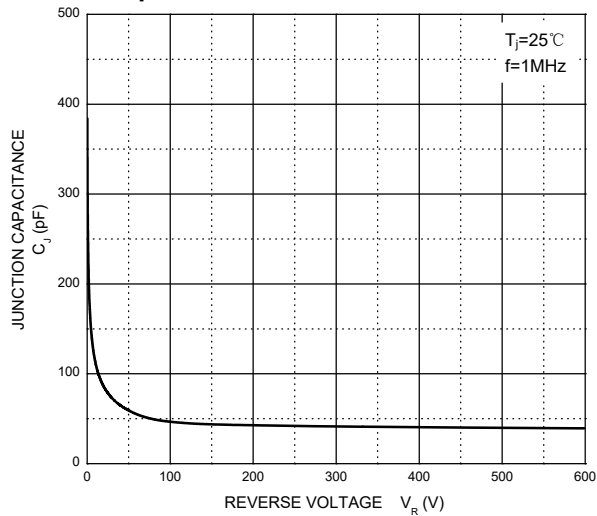
Forward Characteristics



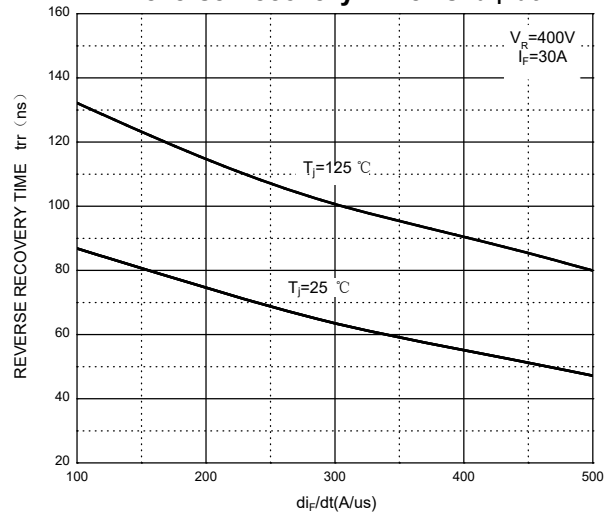
Reverse Characteristics



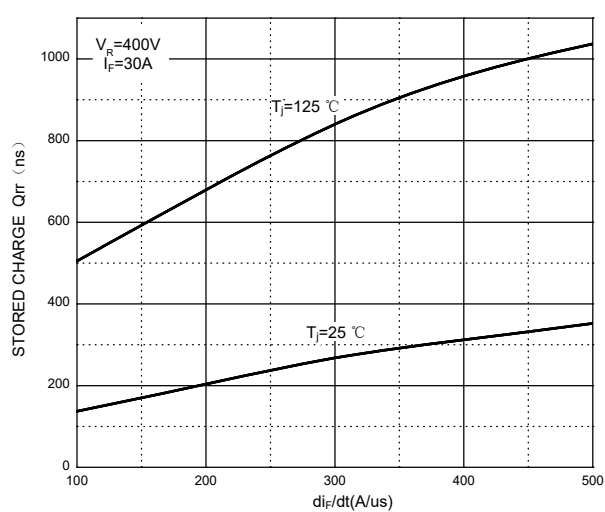
Capacitance Characteristics Per Diode



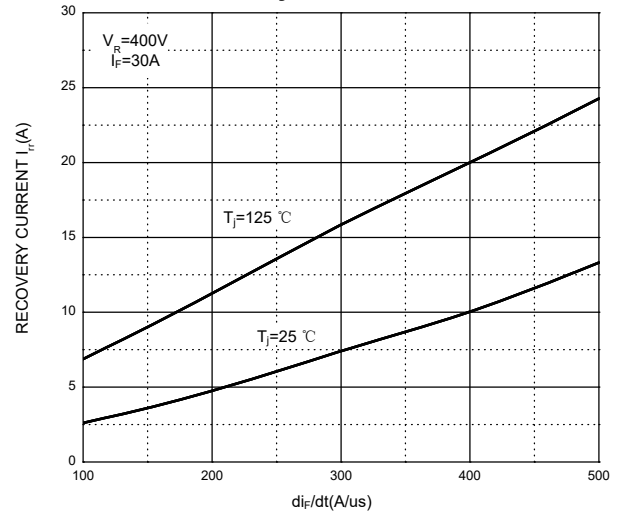
Reverse Recovery Time vs. di_F/dt



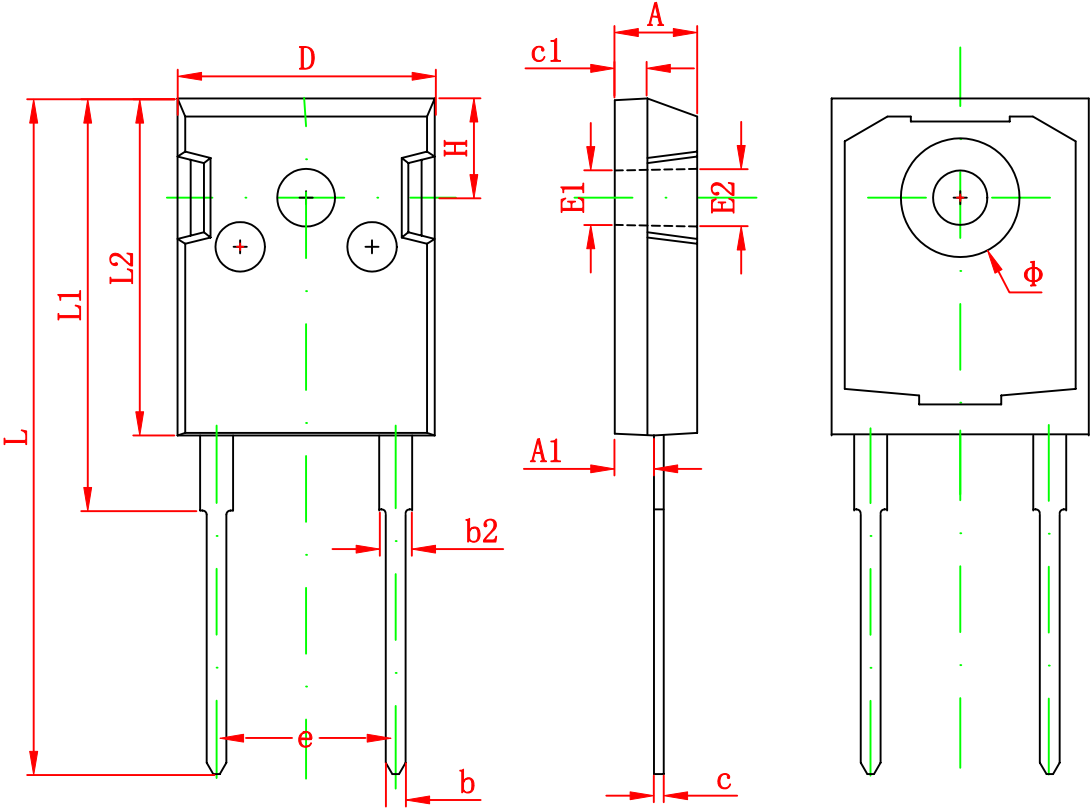
Stored Charge vs. di_F/dt



Recovery Current vs. di_F/dt



TO- 247- 2L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.850	5.150	0.191	0.200
A1	2.200	2.600	0.087	0.102
b	1.000	1.400	0.039	0.055
b2	1.800	2.200	0.071	0.087
c	0.500	0.700	0.020	0.028
c1	1.900	2.100	0.075	0.083
D	15.450	15.750	0.608	0.620
E1	3.500 REF		0.138 REF	
E2	3.600 REF		0.142 REF	
L	40.900	41.300	1.610	1.626
L1	24.800	25.100	0.976	0.988
L2	20.300	20.600	0.799	0.811
Φ	7.100	7.300	0.280	0.287
e	10.86 TYP		0.427 TYP	
H	5.980 REF		0.235 REF	